

Micro Commercial Components 21201 Itasca Street Chatsworth

CA 91311

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MPSA92

Features

• Through Hole Package

Operating & Storage Temperature: -55°C to +150°C

Marking Code: A92

Pin Configuration Bottom View



Electrical Characteristics @ 25°C Unless Otherwise Specified

Electrical characteristics = 25 c chics wise specified					
Symbol	Parameter	Max	Units		
OFF CHARACTERISTICS					
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage* (I _C =-1.0mAdc, I _B =0)	-300		Vdc	
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage (I _C =-100µAdc, I _E =0)	-300		Vdc	
$V_{(BR)EBO}$	Emitter -Base Breakdown Voltage (I _E =-10μAdc, I _C =0)	-5.0		Vdc	
I _{EBO}	Emitter Cutoff Current (V _{EB} =-3.0Vdc, I _C =0)		-0.25	uAdc	
I _{CBO}	Collector Cutoff Current (V _{CB} =-200 Vdc, I _E =0)		-0.25	uAdc	

ON CHARACTERISTICS

h _{FE}	DC Current Gain*			
	(I _C =-1.0mAdc, V _{CE} =-10Vdc)	$(I_C=-1.0 \text{mAdc}, V_{CE}=-10 \text{Vdc}) $ 25		
	(I _C =-10mAdc, V _{CE} =-10Vdc)	80	250	
	(I _C =-50mAdc, V _{CE} =-10Vdc)	25		
V _{CE(sat)}	Collector-Emitter Saturation Voltage			
	$(I_C=-20 \text{mAdc}, I_B=-2.0 \text{mAdc})$		-0.5	Vdc
V _{BE(sat)}	Base-Emitter Saturation Voltage			
	$(I_C=-20\text{mAdc}, I_B=-2.0\text{mAdc})$		-0.9	Vdc

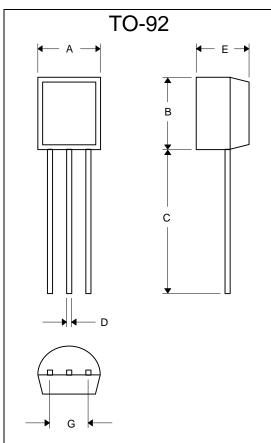
SMALL-SIGNAL CHARACTERISTICS

f_{T}	Current Gain-Bandwidth Product			
	$(I_C=-10\text{mAdc}, V_{CE}=-5\text{Vdc}, f=30\text{MHz})$	50		MHz
C _{cb}	Collector-Base Capacitance			
	$(V_{CB}=-20Vdc, I_{E}=0, f=1.0MHz)$		6.0	pF

*Pulse Width ≤300μs, Duty Cycle≤2.0% MAXIMUM RATINGS

Symbol	Characteristic	MPSA92	Unit
VCEO	Collector-Emitter Voltage	-300	Vdc
V _{СВО}	Collector-Base Voltage	-300	Vdc
VEВО	Emitter-Base Voltage	-5.0	Vdc
lC	Collector Current — Continuous	-300	mAdc
$R_{ heta\mathsf{J}\mathsf{A}}$	Thermal Resistance, Junction to Ambient	200	°C/W
$R_{ heta}$ JC	Thermal Resistance, Junction to Case	83.3	°C/W
PD	Total Device Dissipation @ T _A = 25°C	625	mW
ט י	Derate above 25°C	5.0	mW/°C
P_{D}	Total Device Dissipation @ T _C = 25°C	1.5	Watts
	Derate above 25°C	12	mW/°C

PNP Silicon High Voltage Transistor



DIMENSIONS					
	INCHES MM				
DIM	MIN	MAX	MIN	MAX	NOTE
Α	.175	.185	4.45	4.70	
В	.175	.185	4.46	4.70	
С	.500		12.7		
D	.016	.020	0.41	0.63	
Е	.135	.145	3.43	3.68	
G	.095	.105	2.42	2.67	
D E	.016 .135	.020 .145	0.41 3.43	3.68	



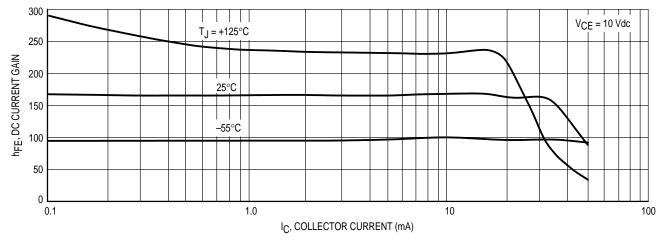


Figure 1. DC Current Gain

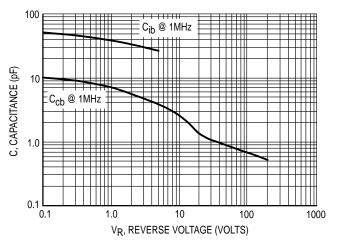


Figure 2. Capacitance

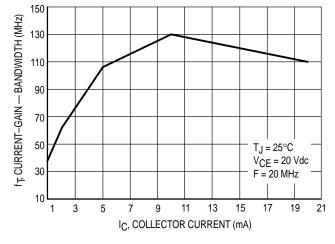


Figure 3. Current-Gain — Bandwidth

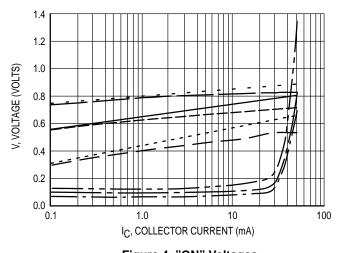


Figure 4. "ON" Voltages

